

# BR2N6488

Rev. C Oct.-2018

## 描述 / Descriptions

TO-220 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-220 Plastic Package.

## 特征 / Features

与 BR2N6491 互补。

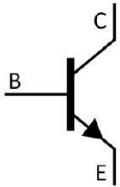
Complement to BR2N6491.

## 用途 / Applications

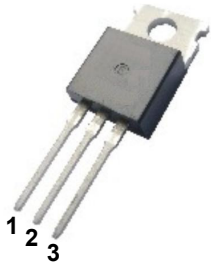
用于通用开关。

Use in general-purpose amplifier and switching applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : Base

PIN 2 : Collector

PIN 3 : Emitter

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

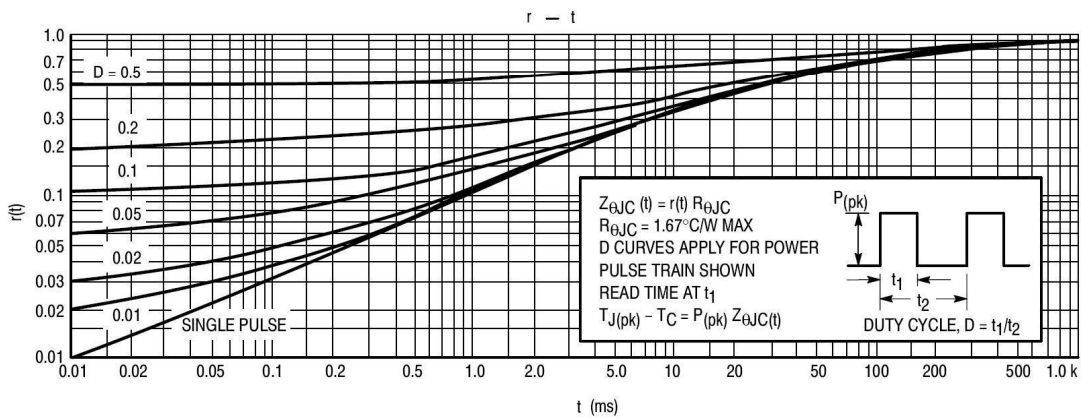
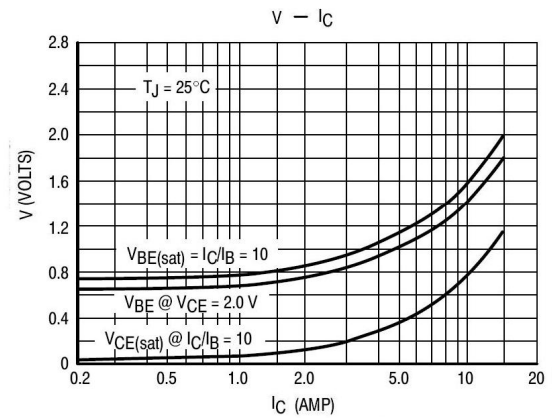
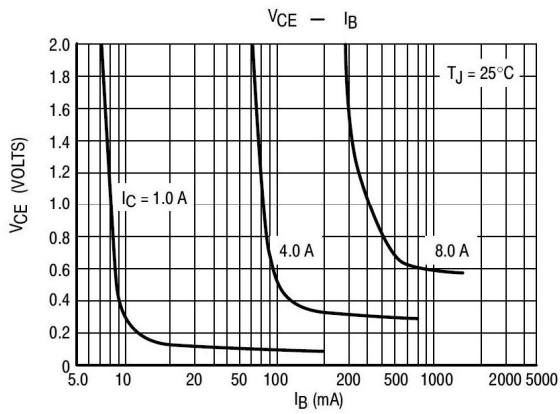
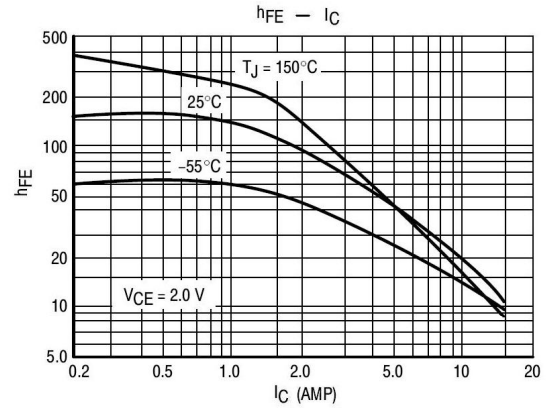
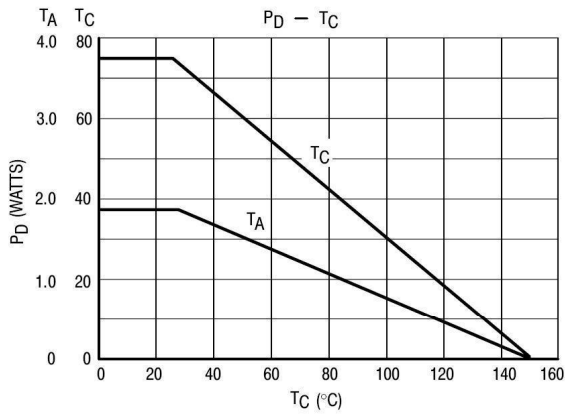
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	$V_{CBO}$	90	V
Collector to Emitter Voltage	$V_{CEO}$	80	V
Emitter to Base Voltage	$V_{EBO}$	5.0	V
Collector Current - Continuous	$I_C$	15	A
Base Current	$I_B$	5.0	A
Total Power Dissipation	$P_D(T_C=25^\circ\text{C})$	75	W
	$P_D(T_A=25^\circ\text{C})$	1.8	W
Operating and Storage Junction Temperature Range	$T_j T_{stg}$	-65~+150	°C
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.67	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	70	°C/W

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C=200\text{mA}$ $I_B=0$	80			V
Collector Emitter Sustaining Voltage	$V_{CEX}$	$I_C=200\text{mA}$ $V_{BE}=1.5\text{V}$	90			V
Collector Cut-Off Current	$I_{CEX}$	$V_{CB}=85\text{V}$ $V_{BE(off)}=1.5\text{V}$			500	$\mu\text{A}$
		$V_{CB}=80\text{V}$ $V_{BE(off)}=1.5\text{V}$ $T_C=150^\circ\text{C}$			5.0	$\mu\text{A}$
Collector Cut-Off Current	$I_{CEO}$	$V_{CE}=40\text{V}$ $I_B=0$			1.0	mA
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=5.0\text{V}$ $I_C=0$			1.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=4.0\text{V}$ $I_C=5.0\text{A}$	20		150	
	$h_{FE(2)}$	$V_{CE}=4.0\text{V}$ $I_C=15\text{A}$	5.0			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5.0\text{A}$ $I_B=0.5\text{A}$			1.3	V
		$I_C=15\text{A}$ $I_B=5.0\text{A}$			3.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	$I_C=5.0\text{A}$ $V_{CE}=4.0\text{V}$			1.3	V
		$I_C=15\text{A}$ $V_{CE}=4.0\text{V}$			3.5	V
Transition Frequency	$f_T$	$I_C=1.0\text{A}$ $f=1.0\text{MHz}$ $V_{CE}=4.0\text{V}$	5.0			MHz
Small-Signal Current Gain	$h_{fe}$	$I_C=1.0\text{A}$ $f=1.0\text{kHz}$ $V_{CE}=4.0\text{V}$	25			

\*Pulse test: pulse width  $\leq 300 \mu\text{s}$ ; duty cycle  $\leq 2\%$ .

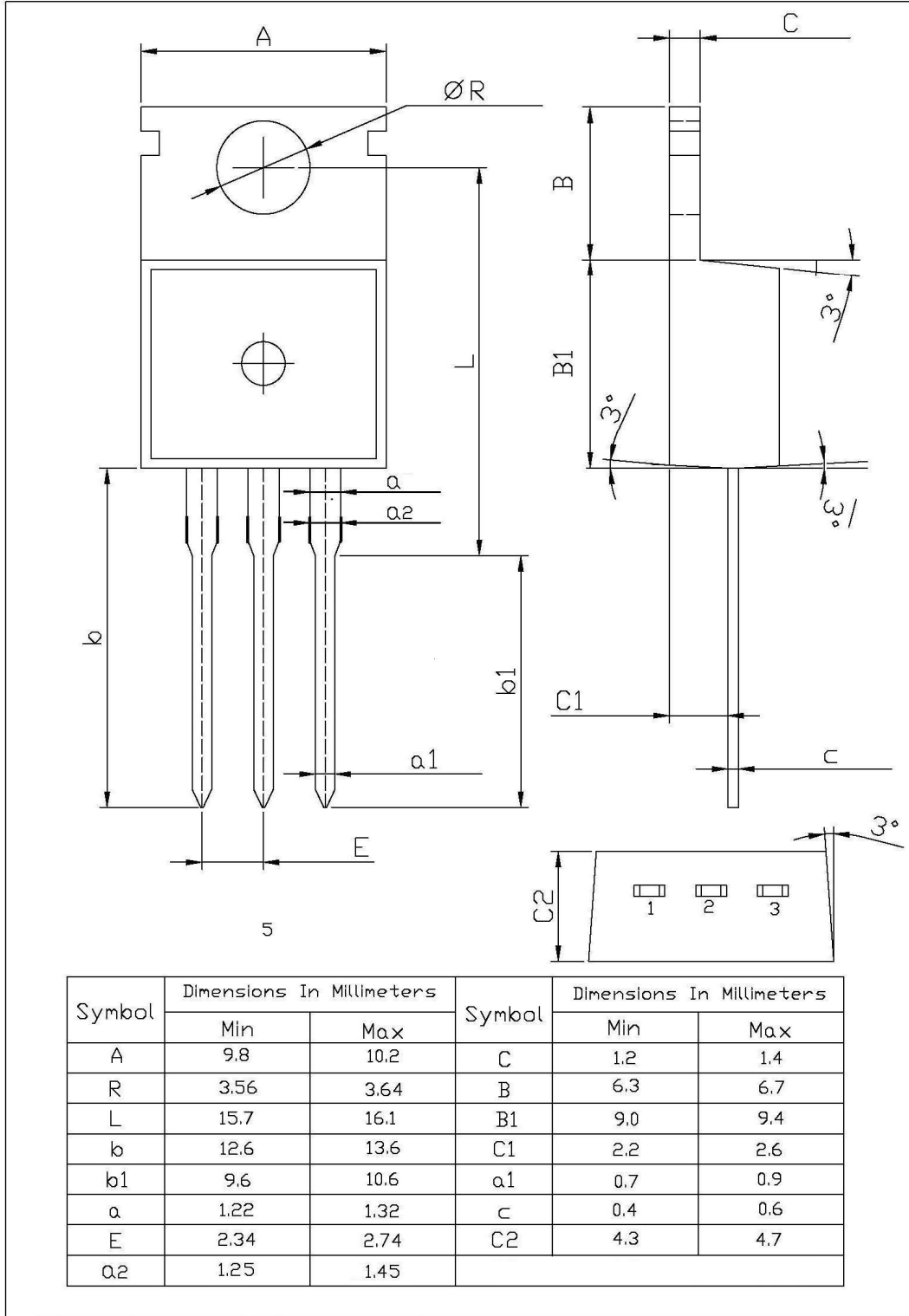
**电参数曲线图 / Electrical Characteristic Curve**



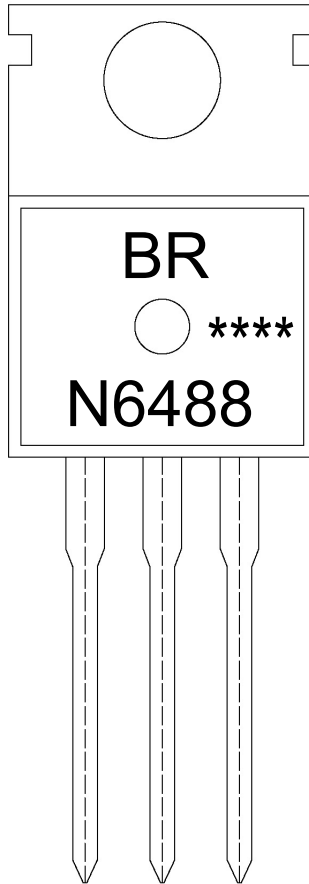
外形尺寸图 / Package Dimensions

T0-220

单位: mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

N6488： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化。

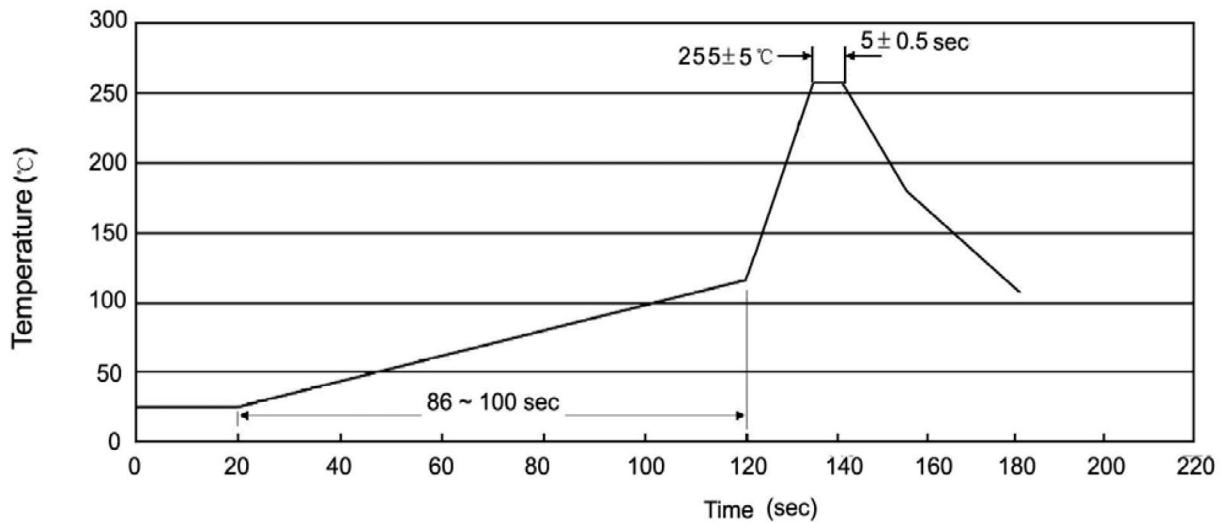
Note:

BR: Company Code

N6488: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

**使用说明 / Notices**